



# 《风光欣》技术资料

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## 2SB1240

## PNP TRANSISTOR

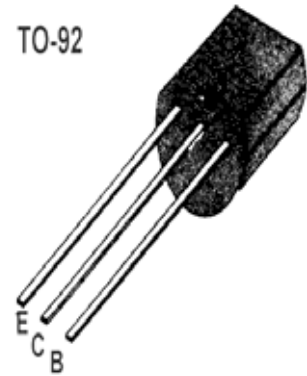
### Features

#### Low $V_{CE(sat)}$

$$V_{CE(sat)} = -0.5V(\text{Typ})(I_c/I_B = -2A/-0.2A)$$

#### ● ABSOLUTE MAXIMUM RATINGS( $T_A=25^\circ\text{C}$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-32	V
Emitter -Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_c$	-2	A
Collector Dissipation	$P_c$	1	W
Junction Temperature	$T_J$	150	
Storage Temperature	$T_{STG}$	-55 ~ +150	



#### ● Electrical characteristics ( $T_a=25^\circ\text{C}$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	-40	-	-	V	$I_c = -50\mu\text{A}$
Collector-emitter breakdown voltage	$BV_{CEO}$	-32	-	-	V	$I_c = -1\text{mA}$
Emitter-base breakdown voltage	$BV_{EBO}$	-5	-	-	V	$I_E = -50\mu\text{A}$
Collector cutoff current	$I_{CBO}$	-	-	-1	$\mu\text{A}$	$V_{CB} = -20\text{V}$
Emitter cutoff current	$I_{EBO}$	-	-	-1	$\mu\text{A}$	$V_{EB} = -4\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-0.5	-0.8	V	$I_c/I_B = -2A/-0.2A$ *
DC current transfer ratio	$h_{FE}$	82	-	390	-	$V_{CE} = -3\text{V}, I_c = -0.5\text{A}$ *
Transition frequency	$f_T$	-	100	-	MHz	$V_{CE} = -5\text{V}, I_E = 0.5\text{A}, f = 30\text{MHz}$
Output capacitance	$C_{ob}$	-	50	-	pF	$V_{CB} = -10\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$

$h_{FE}$  values are classified as follows :

Item	P	Q	R
$h_{FE}$	82~180	120~270	180~390